

Product Overview

FGA40N65SMD: IGBT, 650V, 40A, Field Stop

For complete documentation, see the data sheet.

Using novel field stop IGBT technology, ON Semiconductor's new series of field stop 2nd generation IGBTs offer the optimum performance for solar inverter, UPS, welder, induction heating, telecom, ESS and PFC applications where low conduction and switching losses are essential.

Features

- Maximum junction temperature : $T_J = 175\text{ °C}$
- Positive temperature co-efficient for easy parallel operating
- High current capability
- Low saturation voltage: $V_{CE(sat)} = 1.9V(\text{Typ.}) @ I_C = 40A$
- Fast switching: $E_{OFF} = 6.5\mu J/A$
- Tightened parameter distribution
- RoHS compliant

Applications

- Energy Generation & Distribution
- Uninterruptible Power Supply
- Other Industrial

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	$V_{(BR)CES}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Packaged Diode	Package Type
FGA40N65SMD	1.8657	Pb-free non AEC-Q and PPAP	Active	650	40	1.9	2.1	0.26	0.34	200	3.6	119	-	-	349	Yes	TO-3P-3L

For more information please contact your local sales support at www.onsemi.com.

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